

# 开关电源EMI技术交流

En Li

Mar. 2022

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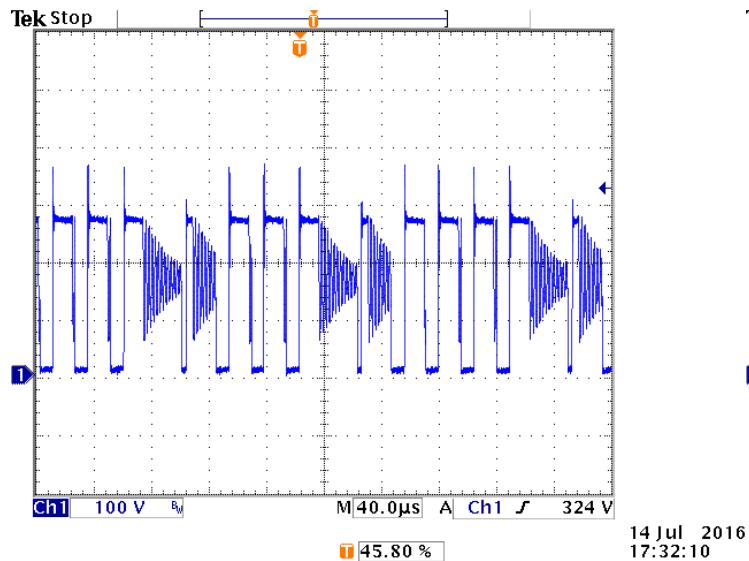
## 主要内容

- 电磁干扰(EMI)分析及处理方案
  - Reducing The Noise Source
  - Improving the Noise Path
- MPS产品介绍

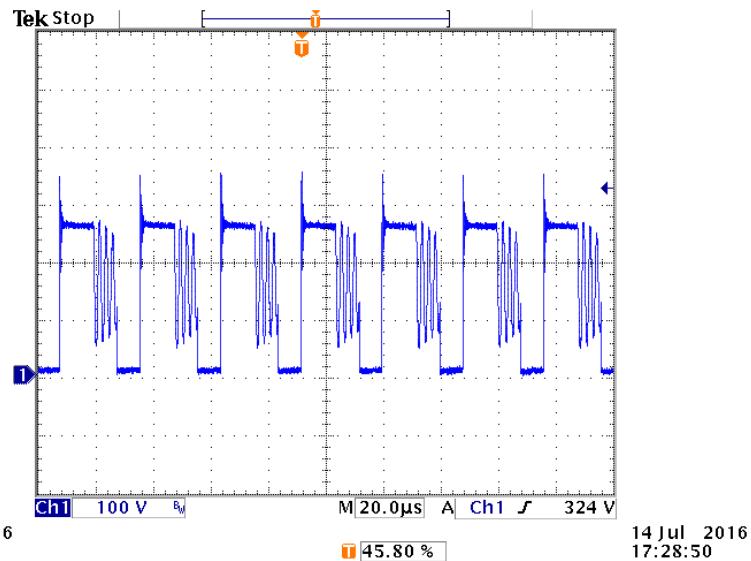


# EMI 危害

大的共模噪声导致芯片工作不正常

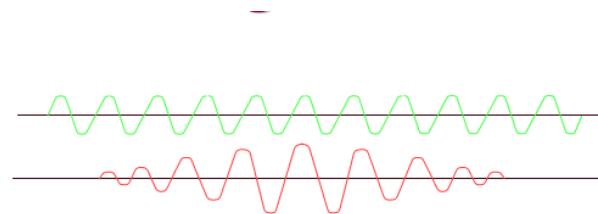


优化后的工作波形



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## 基本概念



Noise Source  $\Rightarrow$  Coupling Path  $\Rightarrow$  Receptor



Suppress  
noise source



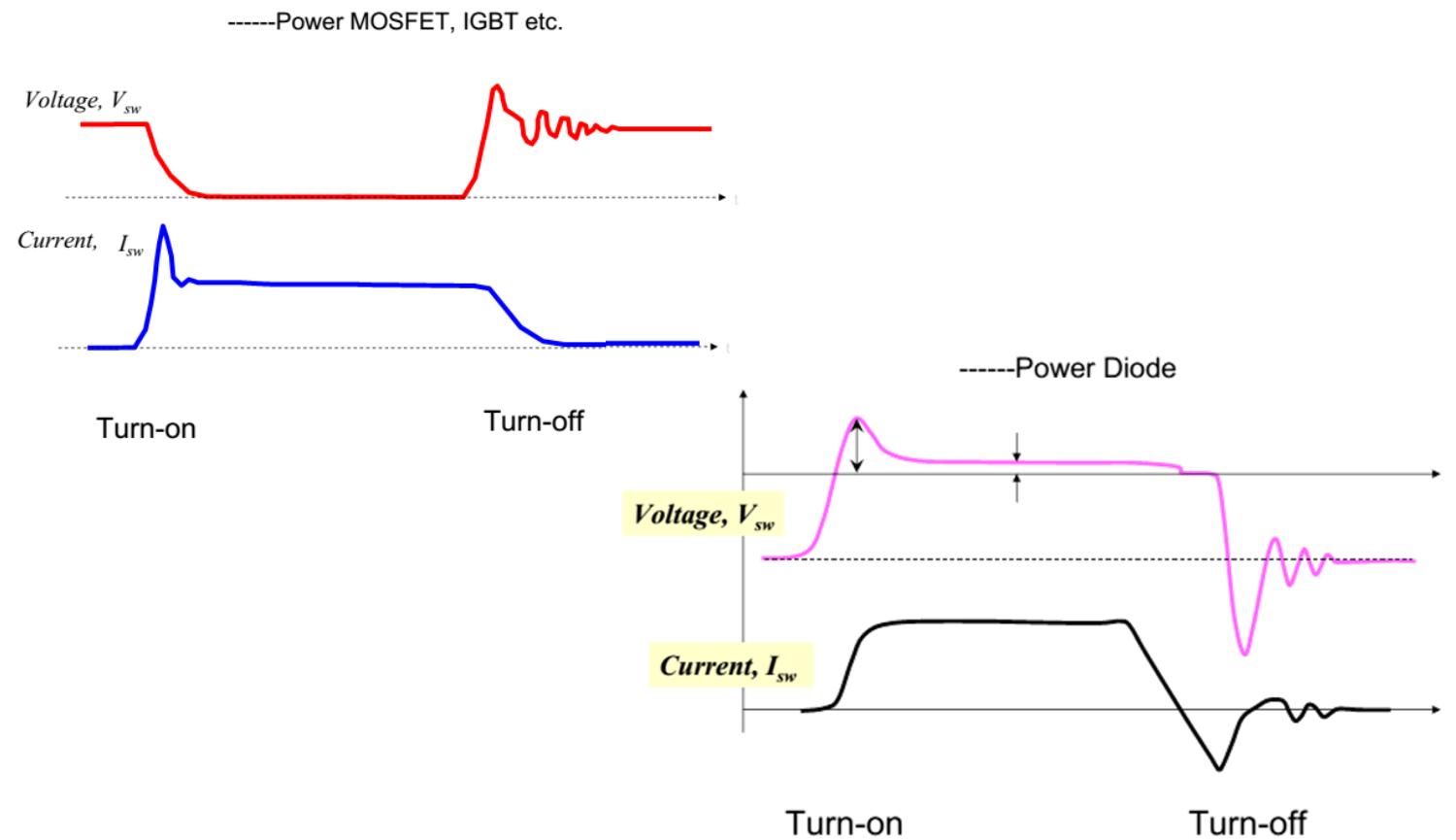
Cut off  
coupling path



Make receptor  
insensitive

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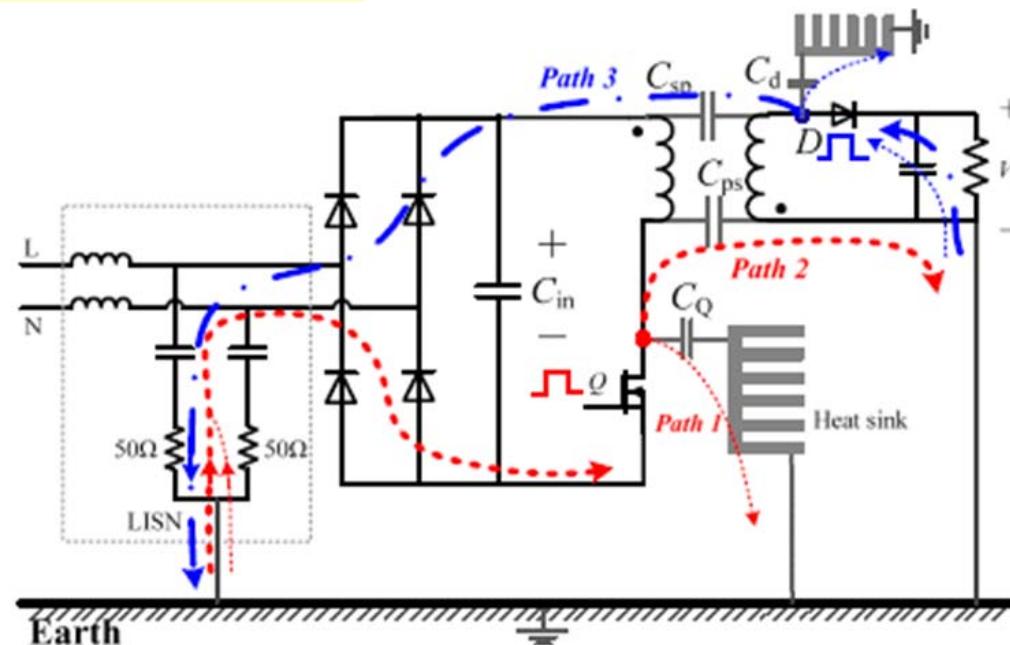
# 开关电源中的主要噪声源



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# 传导 (conducted EMI)

The main noise sources and coupling paths in flyback converter



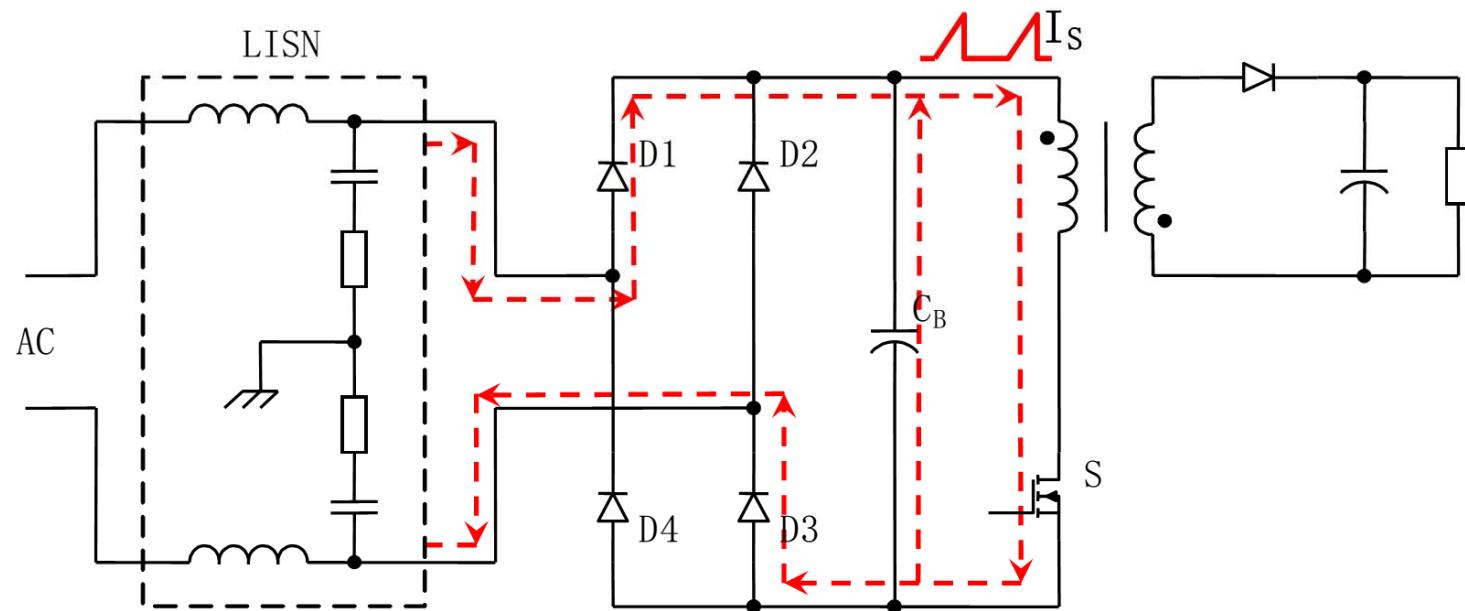
Noise Source: MOSFET, Diode

Coupling path: parasitic capacitance, PCB routing

Load:  $25\Omega$  resistor

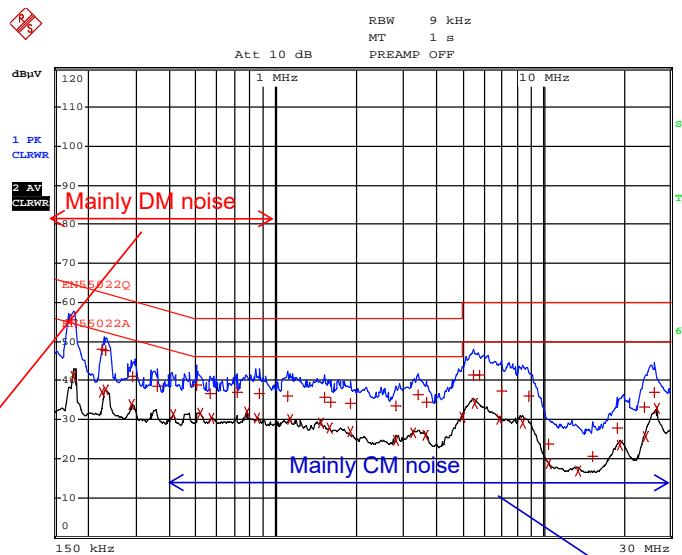
## 传导 (Conducted EMI)

差模噪声耦合路径



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# 传导 (Conducted EMI)



Differential mode noise is mainly current phenomenon and is driven by rapidly changing current signals.

- DM =  $f(dI/dt)$
- DM is associated with voltage across bulk cap created due to switching currents

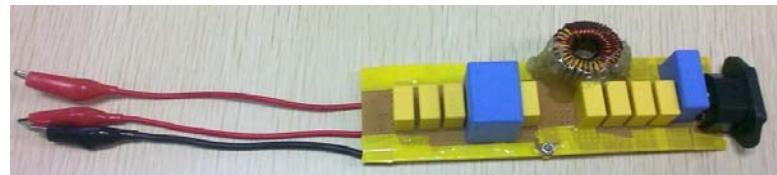
Common mode noise is mainly voltage phenomenon and is driven by rapidly changing voltage signals

- CM =  $f(dV/dt)$
- CM can be associated with capacitive coupling and displacement currents external to the power supply

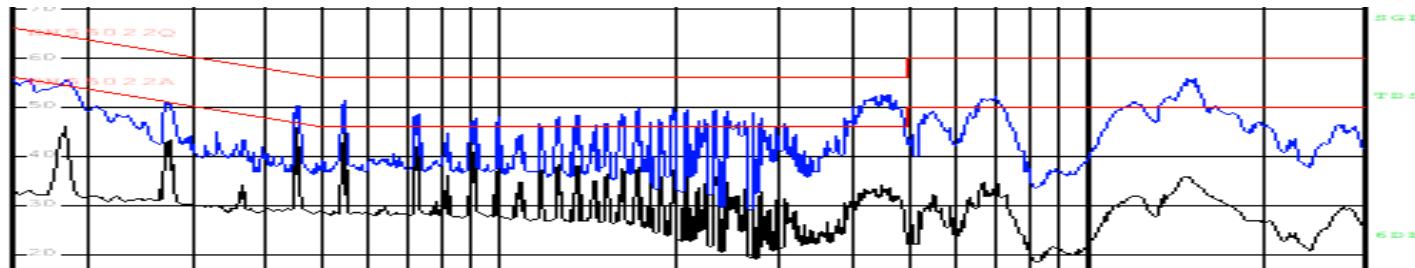
# 传导 (Conducted EMI)

## 传导电磁干扰改善步骤

- ❖ 用滤波器来区分共模与差模干扰;



- ❖ 根据频率分布来确定主导的电磁干扰;



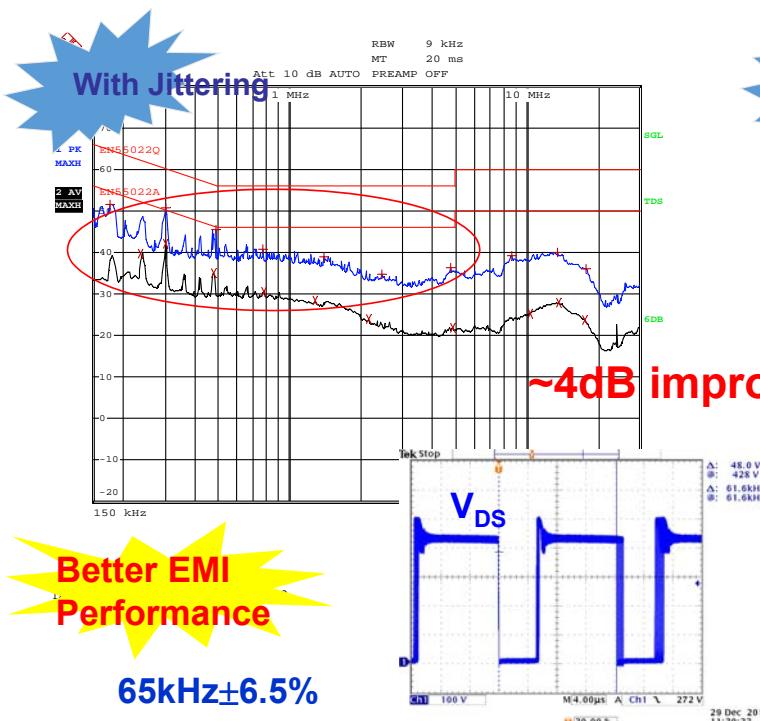
- 主要差模
- 低次谐波
- 交流整流相关
- 近场干扰
- ...

- 差模与共模
- 高次谐波
- 低频震荡
- 近场干扰
- ...

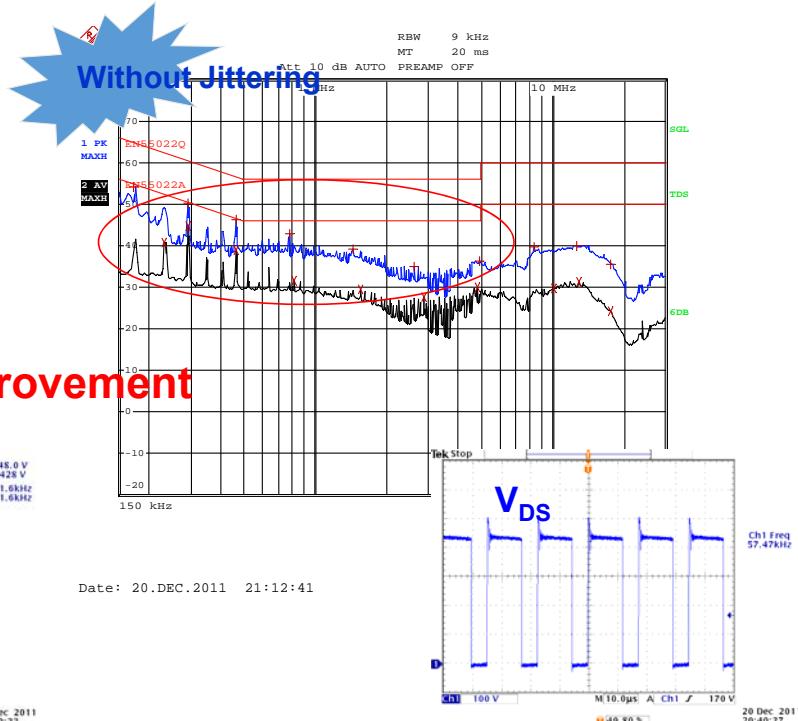
- 共模
- 近场干扰
- 高频振荡
- 开关上升下降沿
- 二极管反向恢复
- Layout
- ...

# 传导 (Conducted EMI)

Frequency Jittering



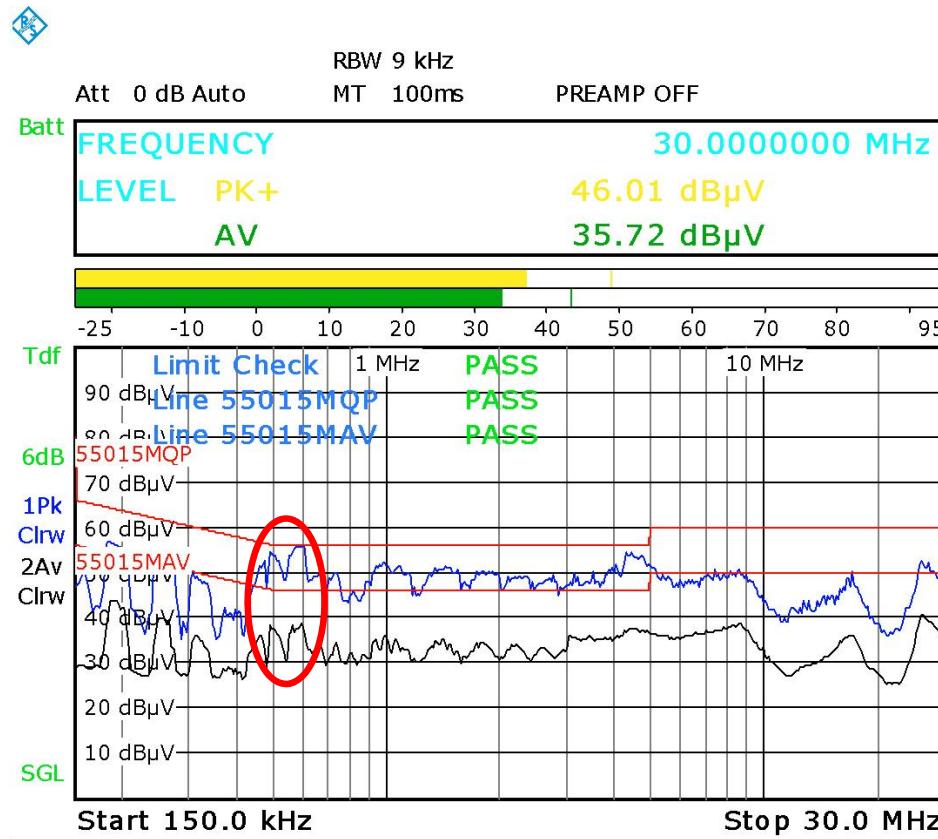
Test condition:  $V_{IN}=220VAC/50Hz$ ,  $V_o=12V$ ,  $I_o=3A$



Frequency jittering which leads to better EMI performance.

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# 传导 (Conducted EMI)



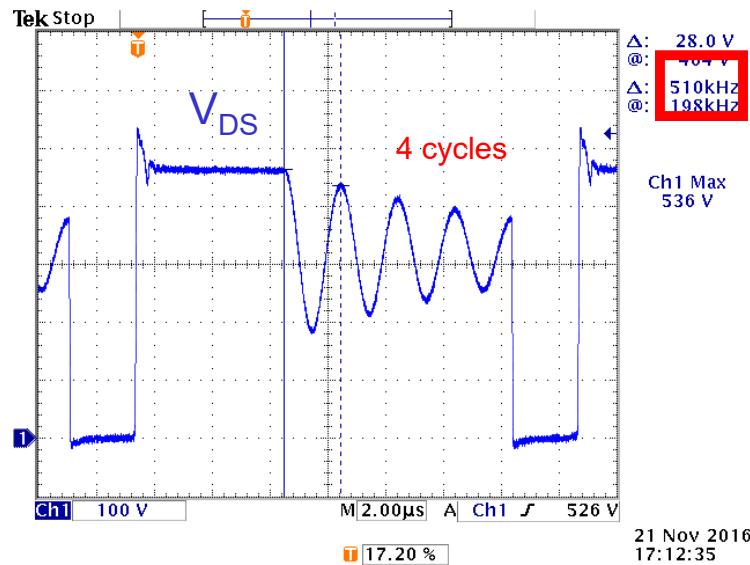
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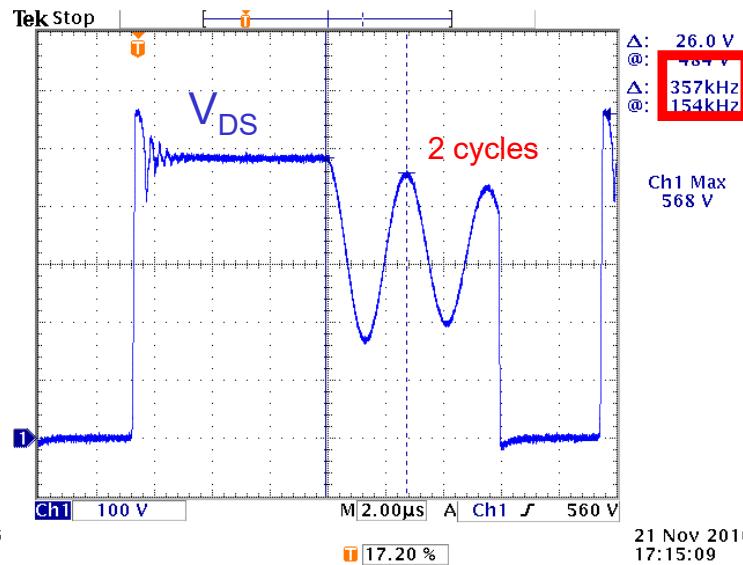
# 传导 (Conducted EMI)

Test Condition: Vin=230VAC, Output=20V/2.25A

L=365uH, N=7, K@90VAC=I<sub>ripple</sub>/I<sub>peak</sub>=1.



L=740uH, N=8, K@90VAC=I<sub>ripple</sub>/I<sub>peak</sub>=0.7.



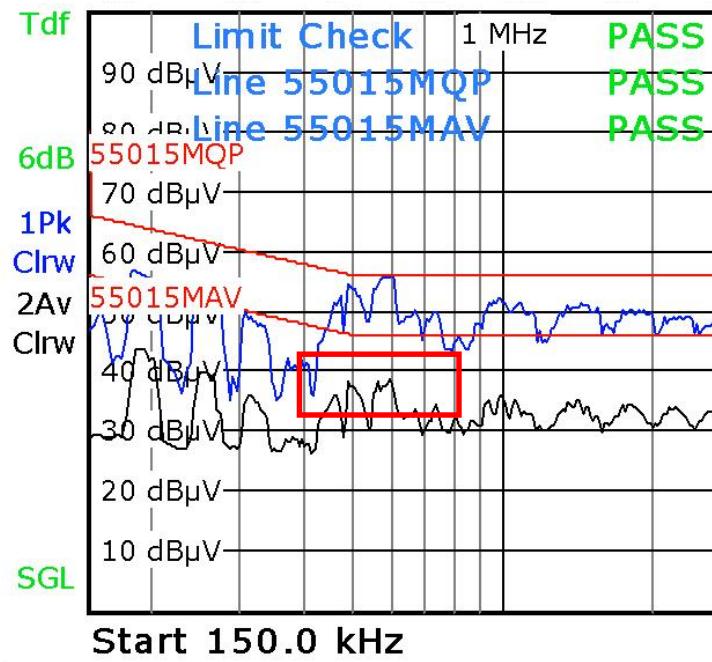
When the system enter DCM, the oscillation is determined by primary inductance L and parasitic capacitor (MOS and transformer ).

The oscillation frequency is hundreds kHz, it's hard to get enough EMI margin.

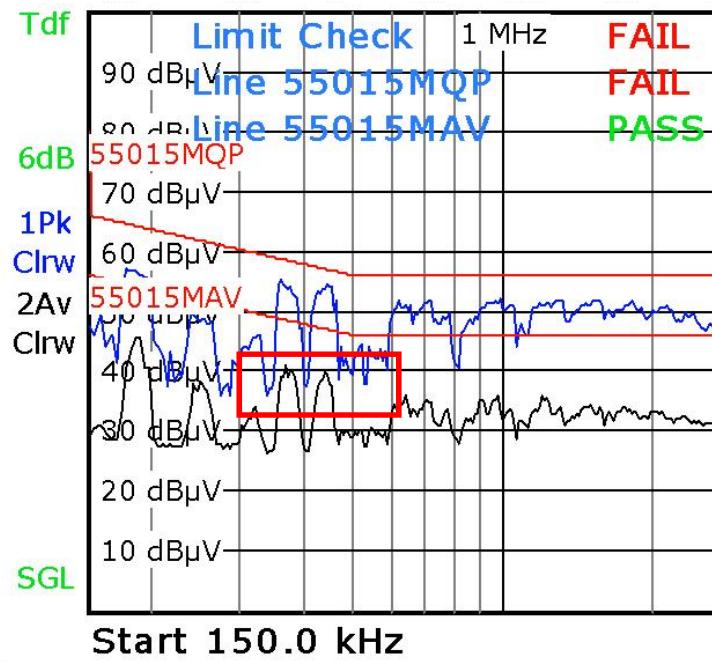
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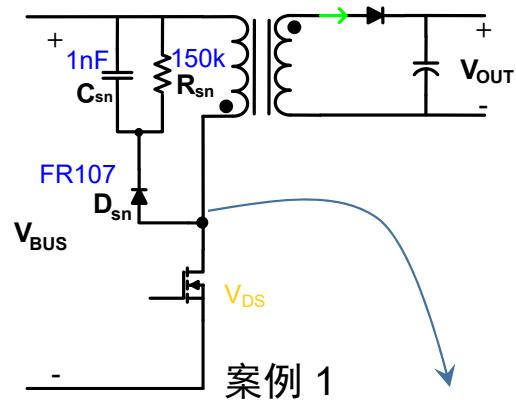
L=740uH, N=8, K@90VAC= $I_{\text{ripple}}/I_{\text{peak}}=0.7$ .



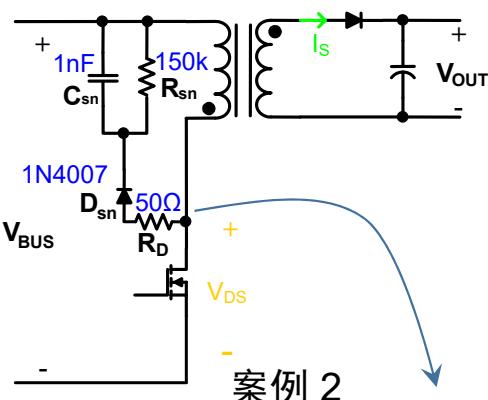
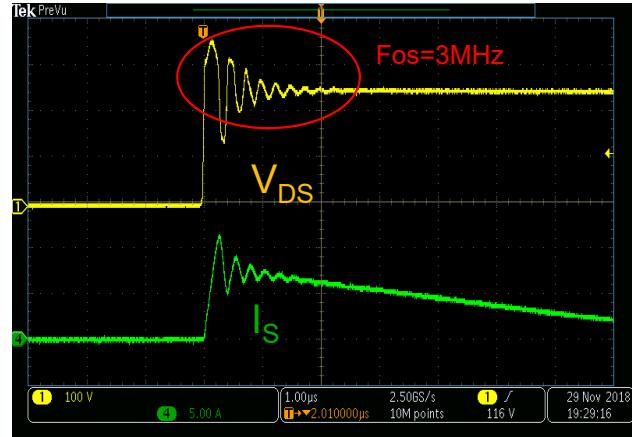
Increasing inductor can reduce frequency, and chooses smaller K can reduce the cycles.

# 传导 (Conducted EMI)

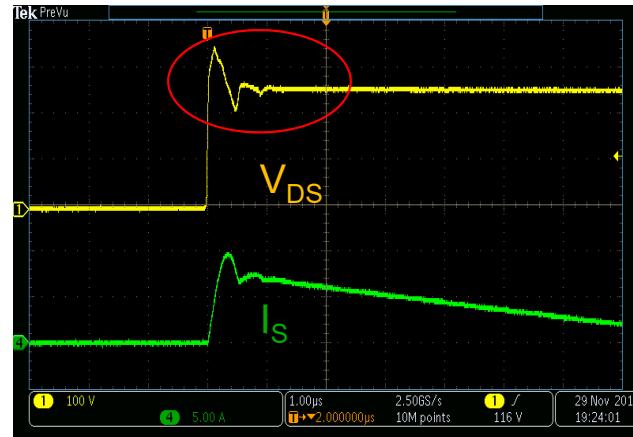
- ❖ 改善效果快速判定方法



案例 1



案例 2



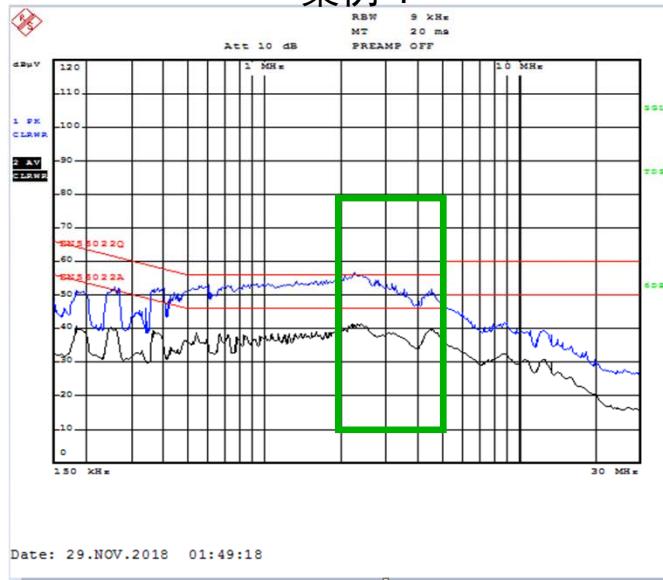
通过改变原边Mosfet关断时VDS的震荡来改善EMI

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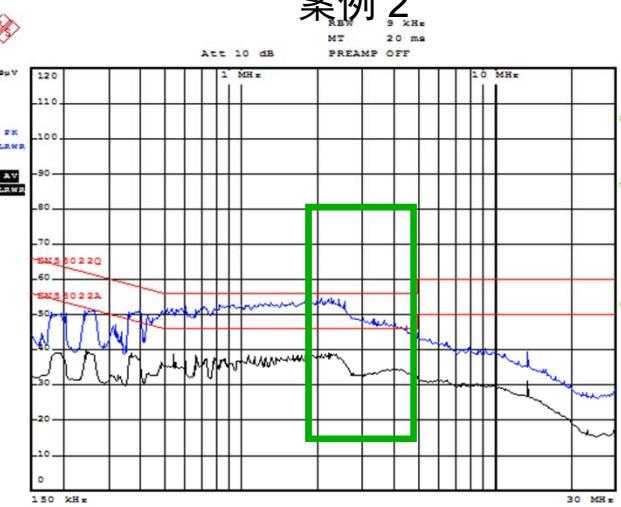
# 传导 (Conducted EMI)

- ❖ 改善效果快速判定方法

案例 1



案例 2

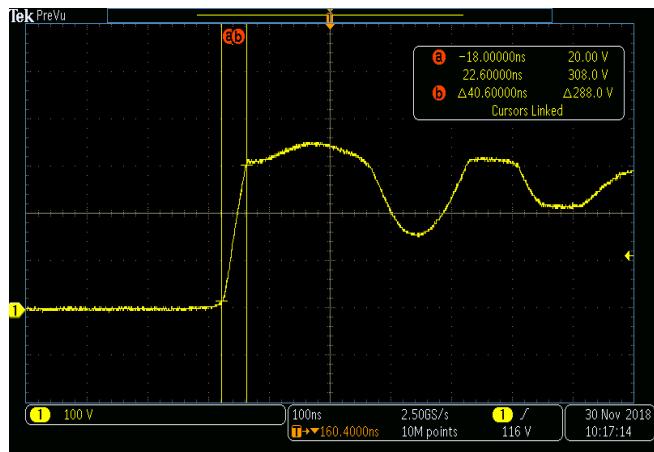


传导EMI在3MHz段有~5dB改善

# 传导 (Conducted EMI)

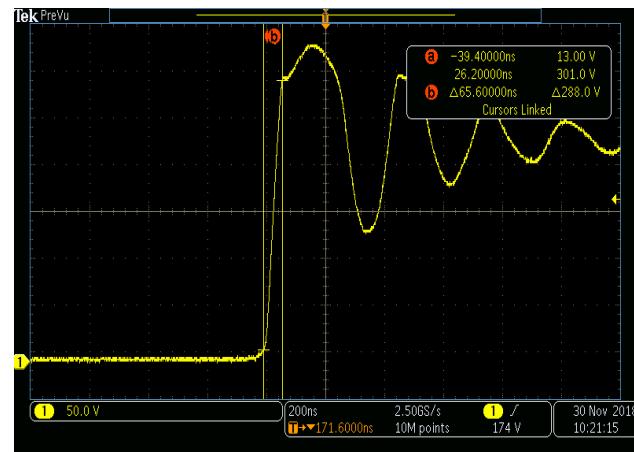
- ❖ 改善效果快速判定方法

案例 1



$$1/(\pi * \text{tr1}) = 7.8\text{MHz}$$

案例 2



$$1/(\pi * \text{tr2}) = 4.9\text{MHz}$$

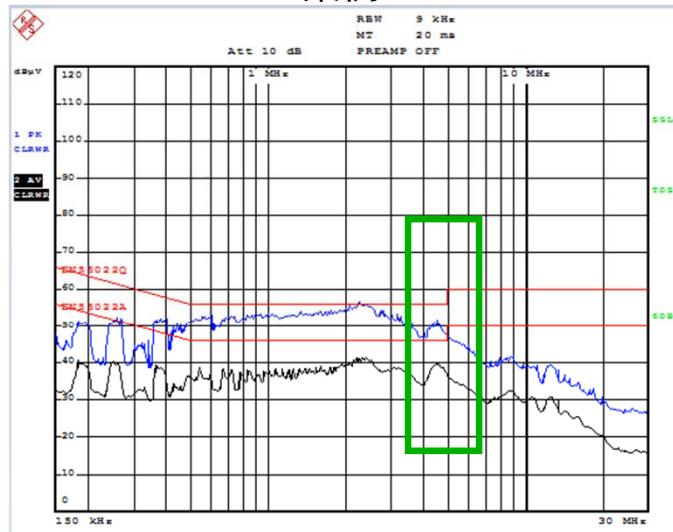
改变VDS的上升/下降斜率来改善EMI

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# 传导 (Conducted EMI)

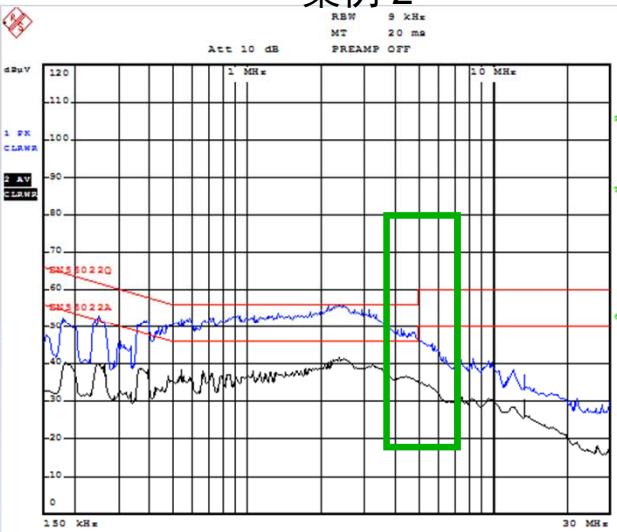
- ❖ 改善效果快速判定方法

案例 1



Date: 29.NOV.2018 01:49:18

案例 2



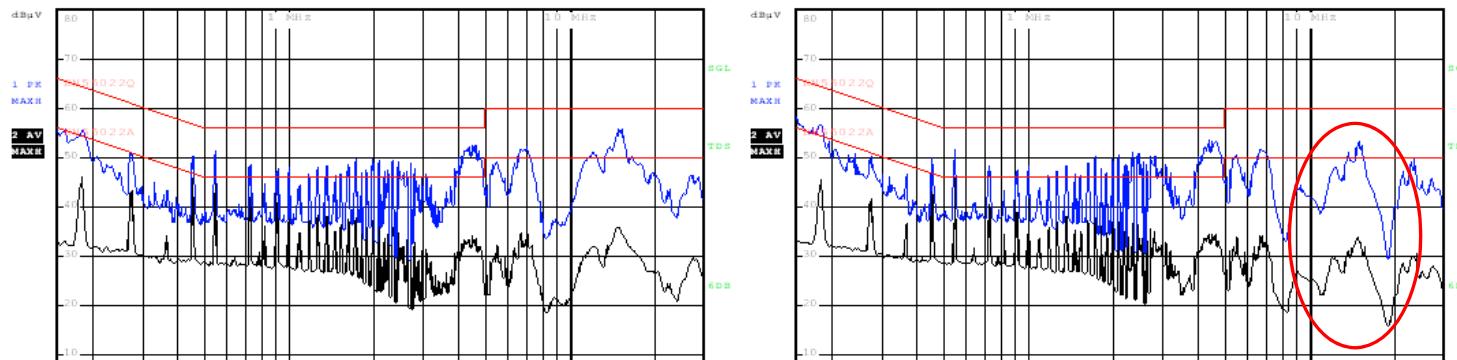
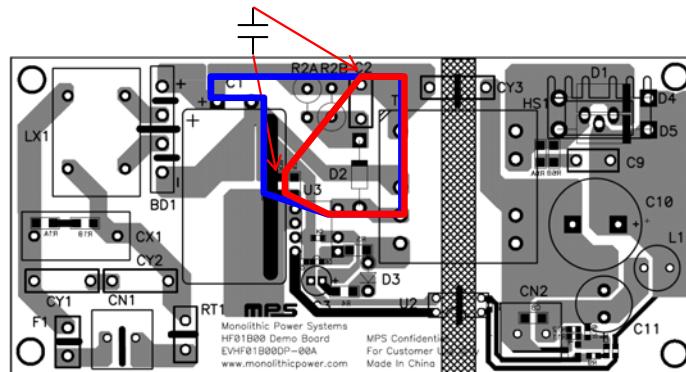
Date: 29.NOV.2018 19:56:21

传导EMI在5MHz段有~3dB改善

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# 传导 (Conducted EMI)

❖ 减小传导电磁干扰途径一 - 改善电路板的布线



传导EMI在10MHz+段有~3dB改善

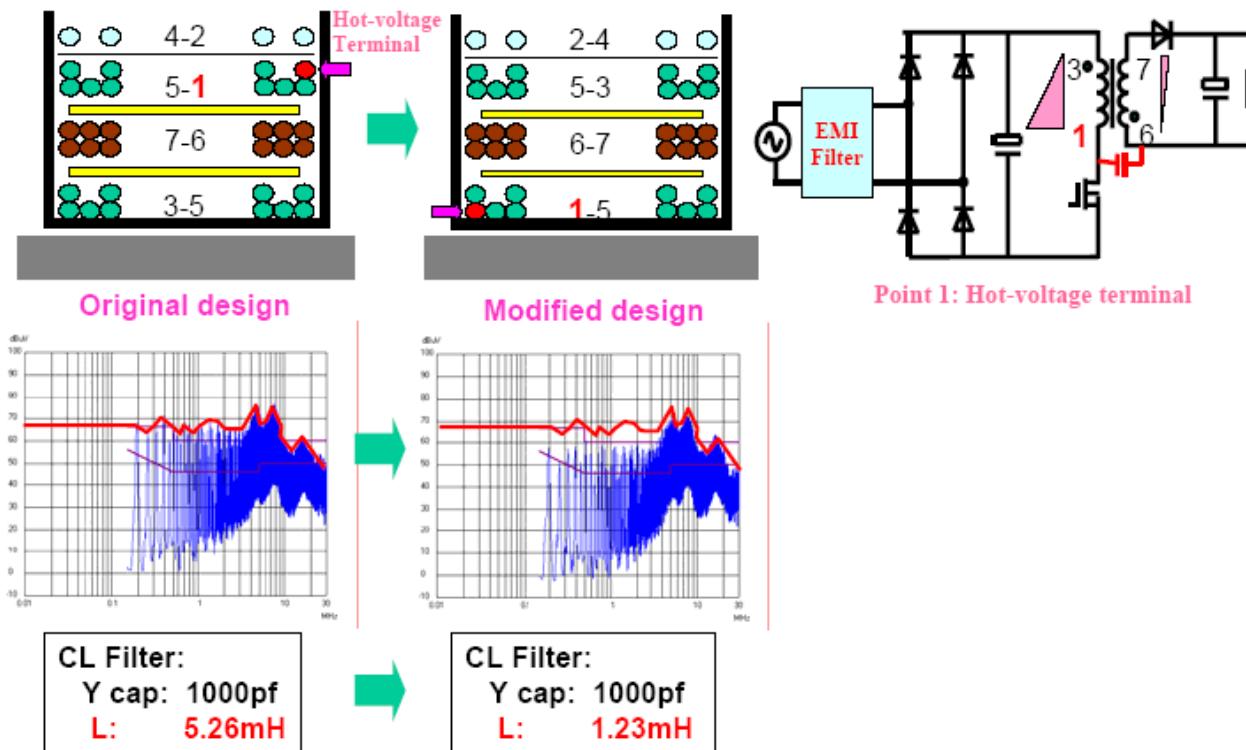
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## 传导 (Conducted EMI)

- Y capacitors
- Common mode filters (Common Choke)
- Better transformer construction techniques aimed at reducing CM noise at its source thus reducing the need for heavy filtering using CM line filters and Y capacitors
  - Basic transformer construction recommendations
  - Use of Shield windings
- Near field coupling

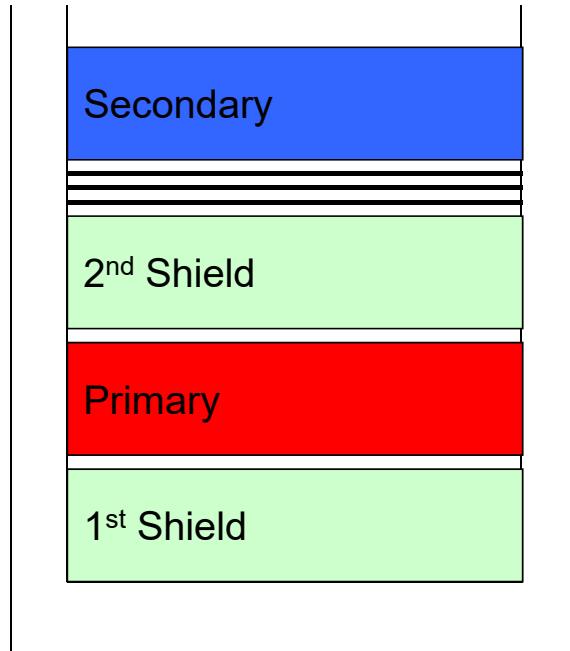
# 传导 (Conducted EMI)

Effects of terminal position on conducted EMI noise



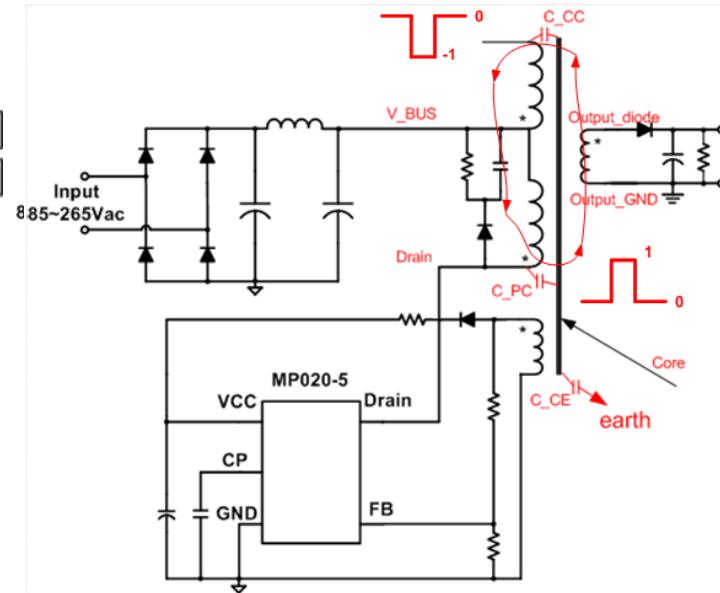
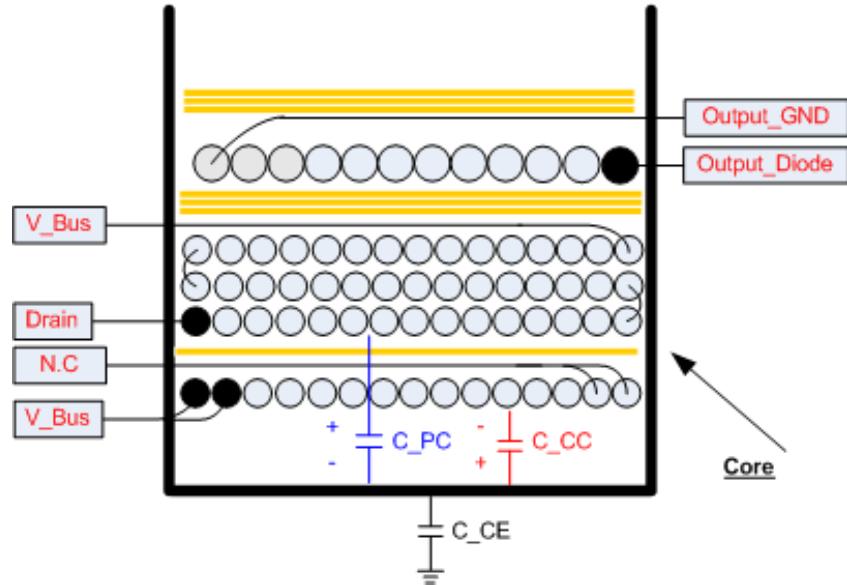
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## 传导 (Conducted EMI)



- Generally 2 separate shield windings are recommended
  - 1<sup>st</sup> shield is the “Cancellation Shield winding” and is normally placed between core and primary winding
  - 2<sup>nd</sup> shield is the “Balanced Shield winding” placed between the Primary and the Secondary windings

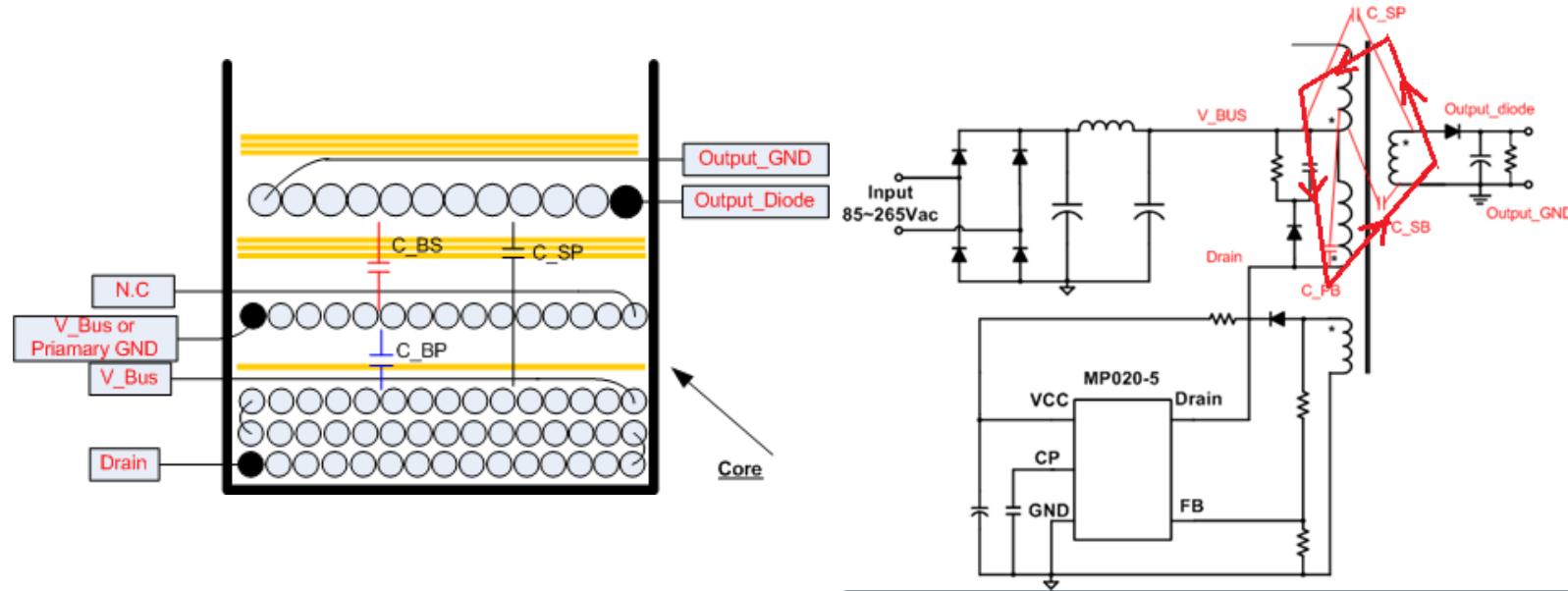
# 传导 (Conducted EMI)



- Cancels out the P-E noise mechanism
- Generally uses around  $\frac{1}{2}$  the number of turns in the first layer of primary winding (should be tuned by the evaluation)
- Both the primary and cancellation windings induce displacement currents in opposite directions, leading to “cancellation” of displacement currents within the LISN

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# 传导 (Conducted EMI)

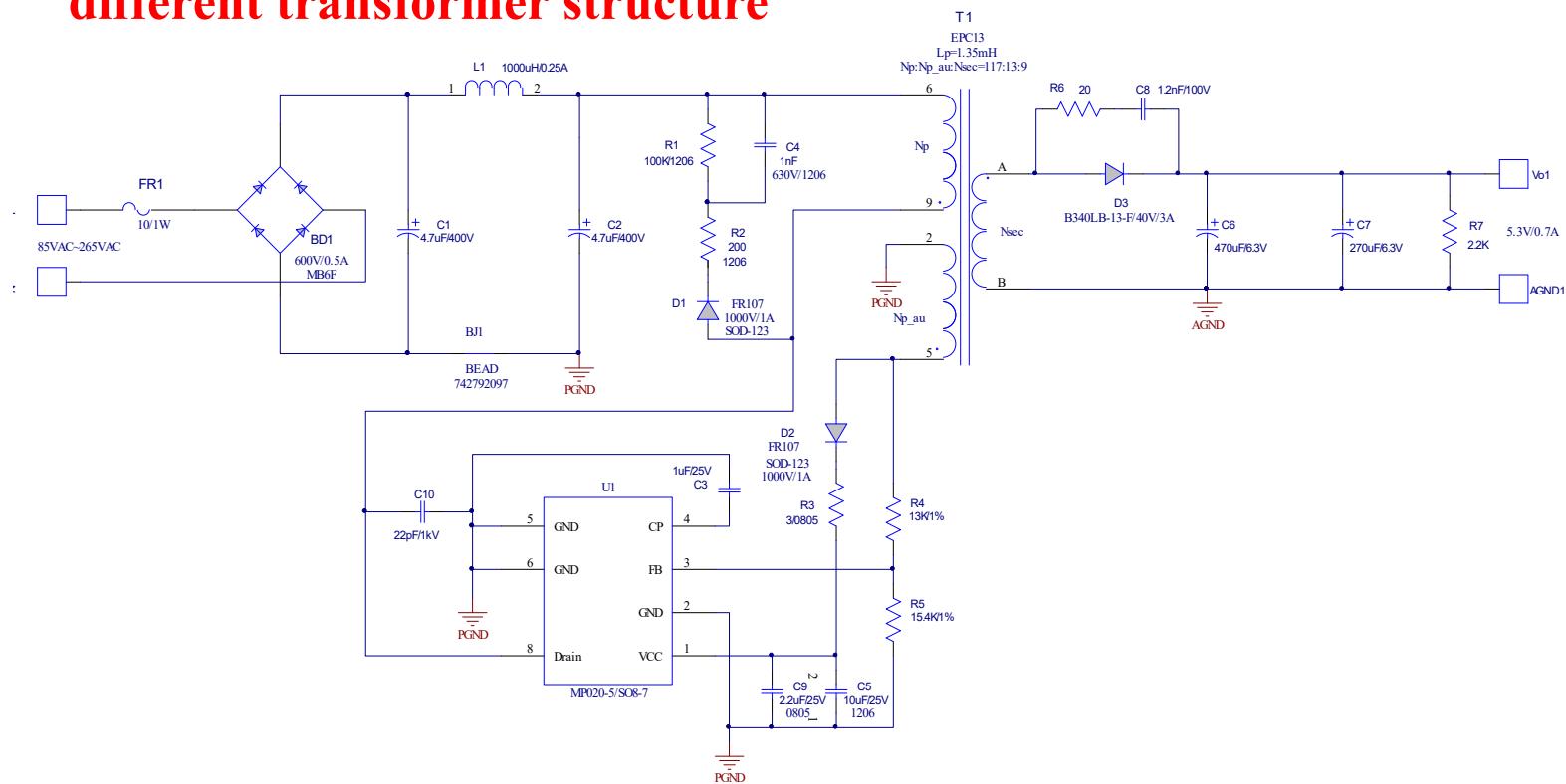


- Used to reduce P-S coupling mechanism
- Generally uses 1-2 turns less than the secondary winding
- Principle is to “balance” the potential at the primary & secondary side thereby reducing noise coupling

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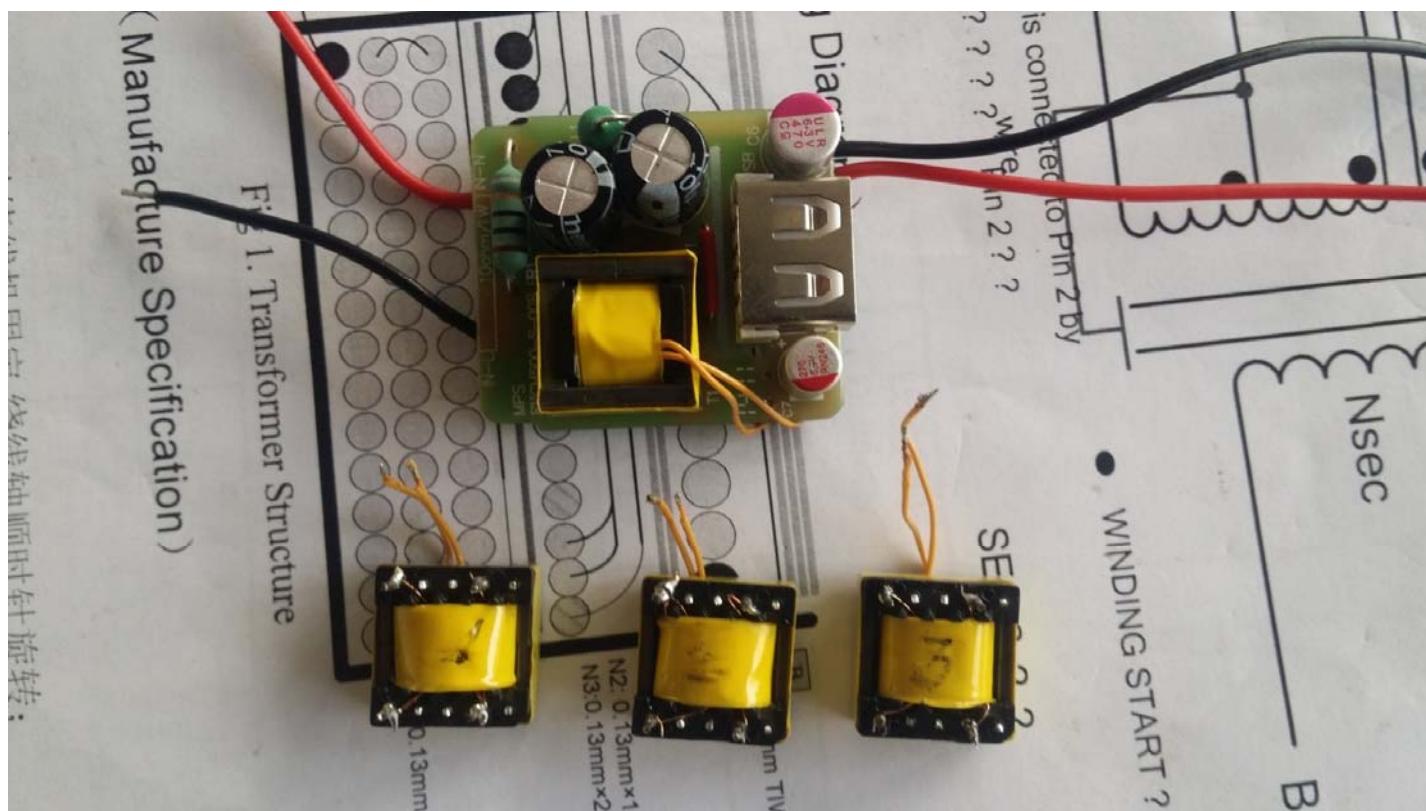
# 传导 (Conducted EMI)

The following test results is based on the same SCH except the different transformer structure



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# 传导 (Conducted EMI)



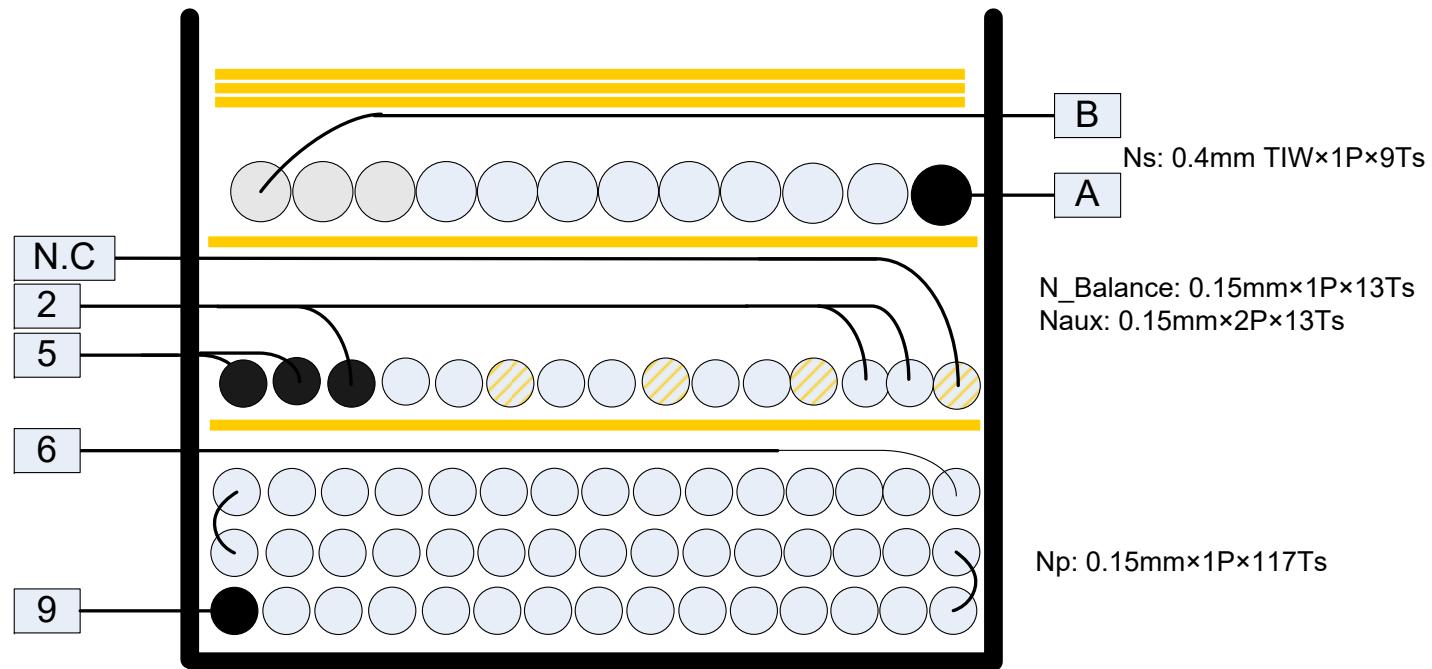
(Manufacture Specification)

Fig 1. Transformer Structure

● 1. 电源线的连接：必须将地线和时钟线连在一起：

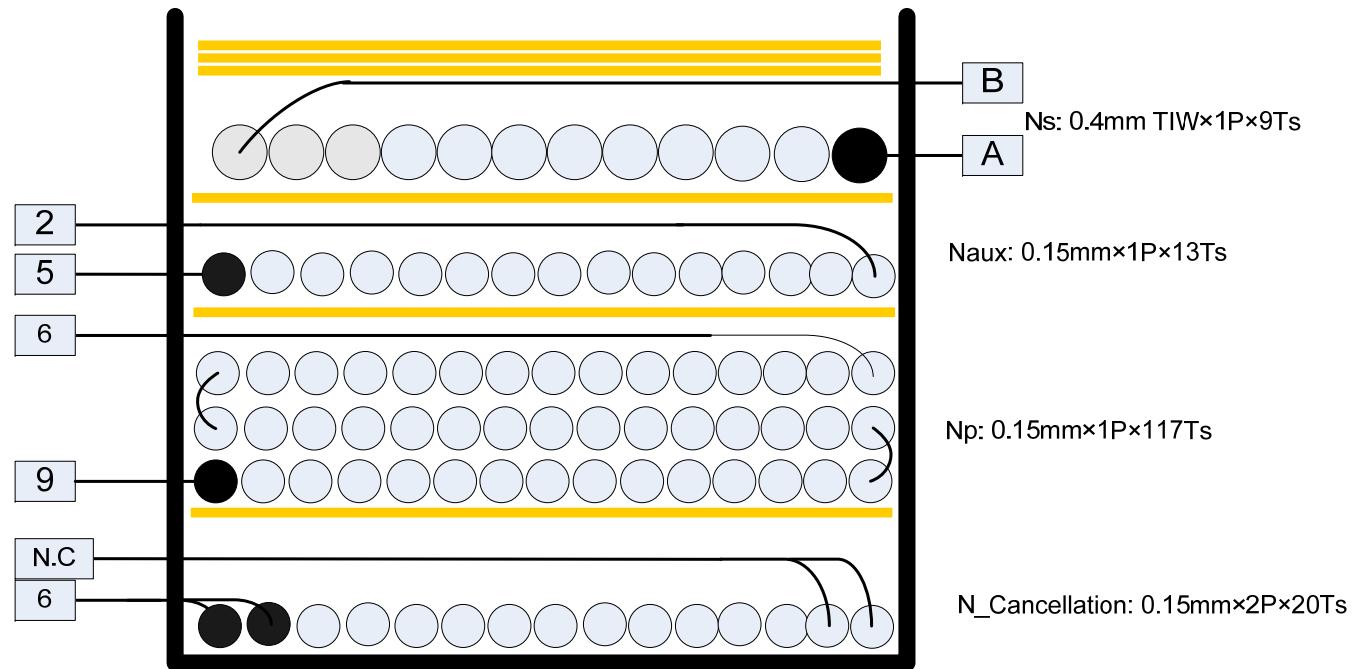
**mPS**

## 传导 (Conducted EMI)



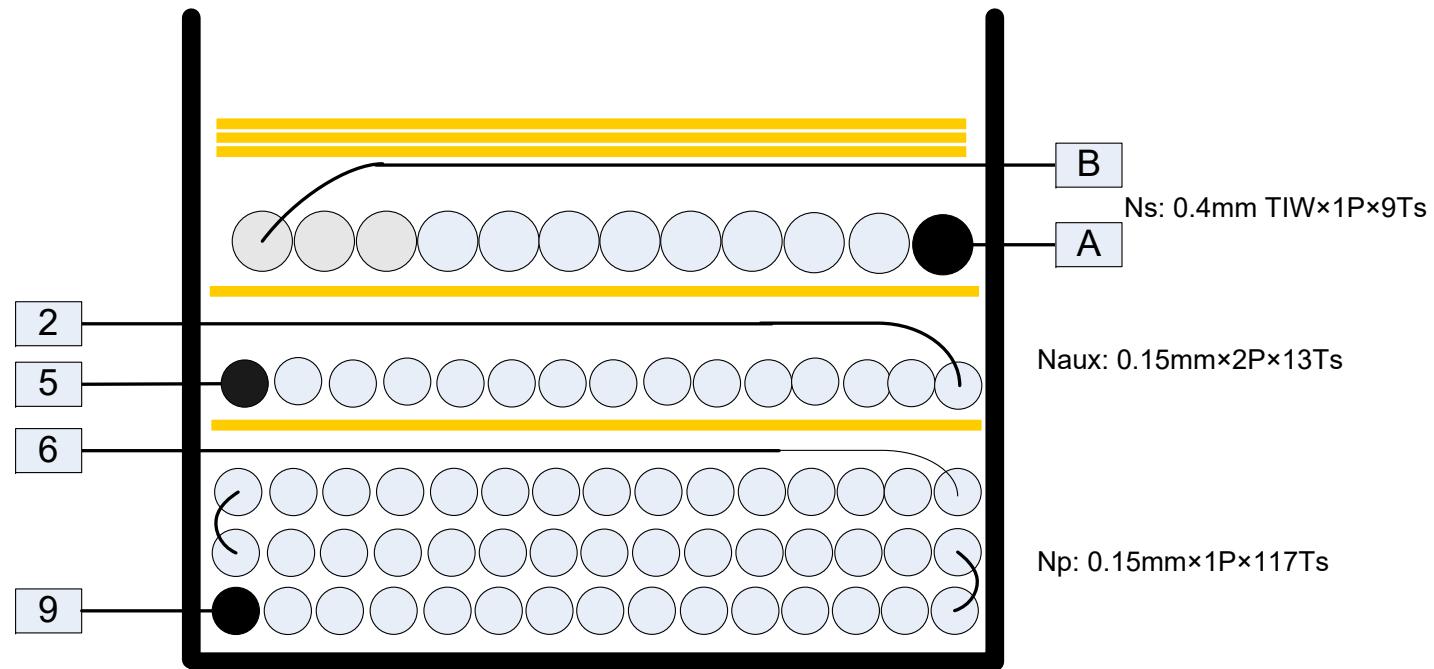
**Xformer #1 W/I balance winding, which wound with the auxiliary winding**

## 传导 (Conducted EMI)



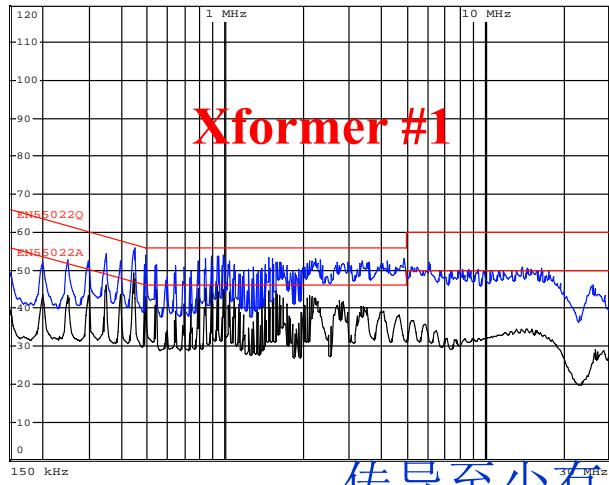
Xformer #2 W/I cancellation winding

## 传导 (Conducted EMI)

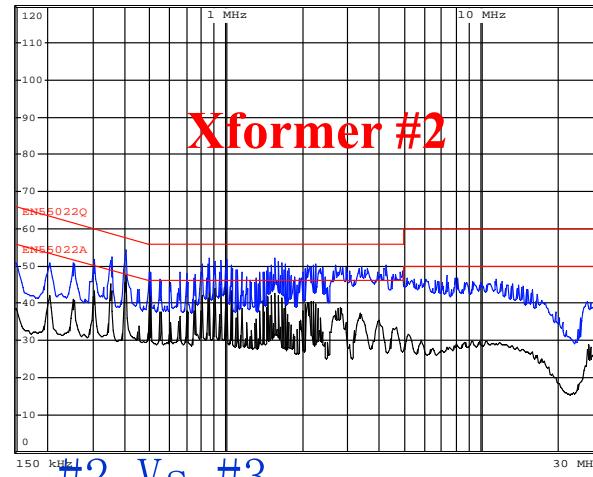


Xformer #3 W/O any cancellation or balance winding

## 传导 (Conducted EMI)

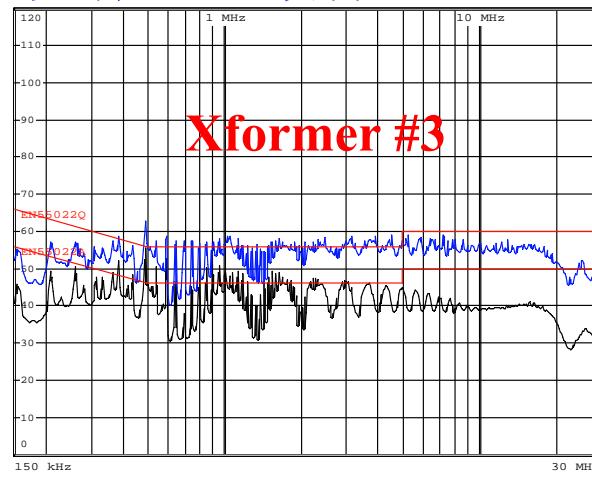


Xformer #1



Xformer #2

传导至少有4~5dB改善#1, #2 Vs #3

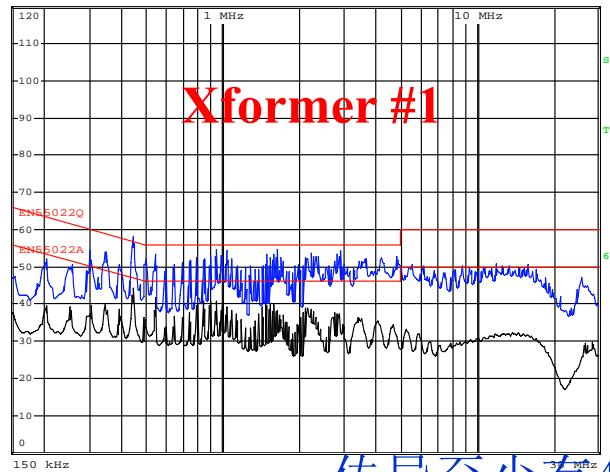


Xformer #3

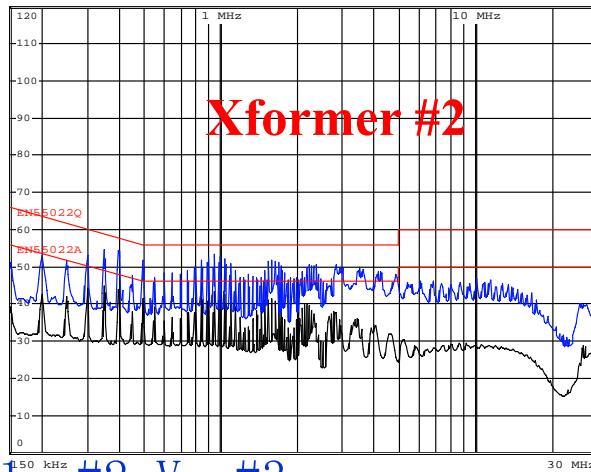
**Test conditions:**  
**220Vac input**  
**5.3V/0.7A output**  
**L line**

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## 传导 (Conducted EMI)

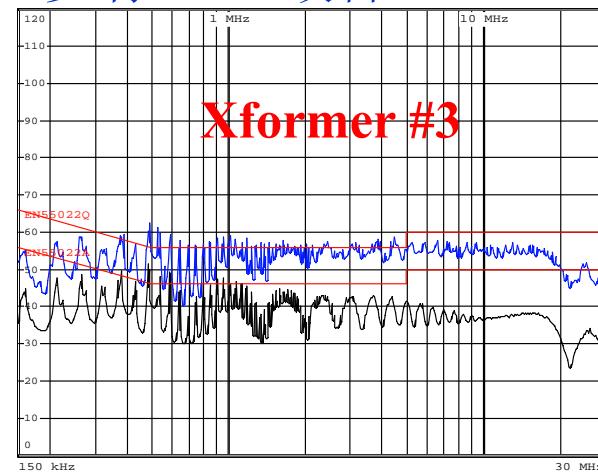


Xformer #1



Xformer #2

传导至少有4~5dB改善#1, #2 Vs #3



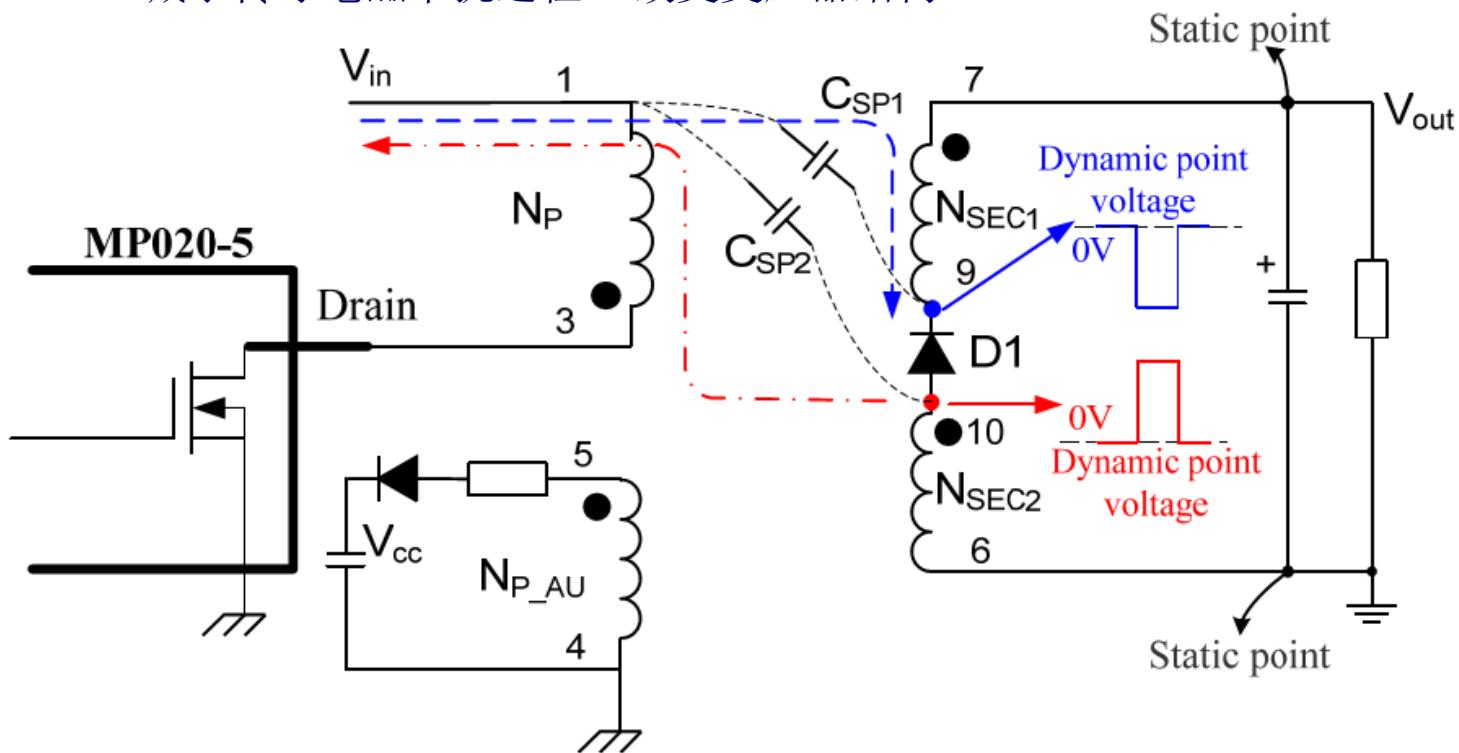
Xformer #3

**Test conditions:**  
**220Vac input**  
**5.3V/0.7A output**  
**N line**

**mPS**

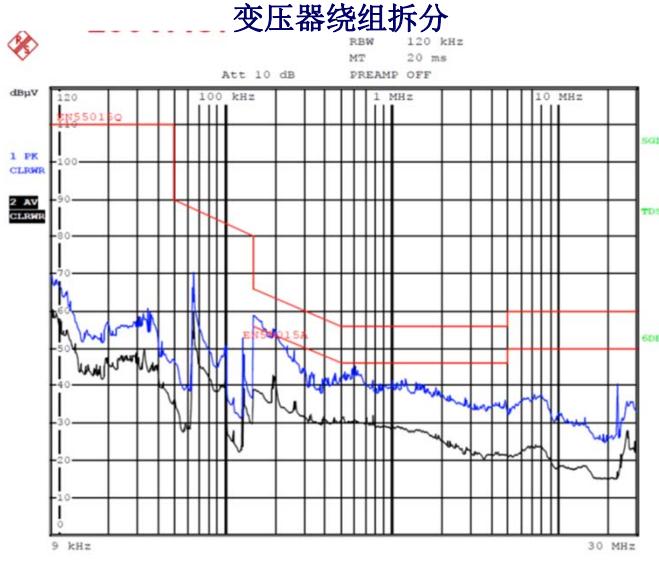
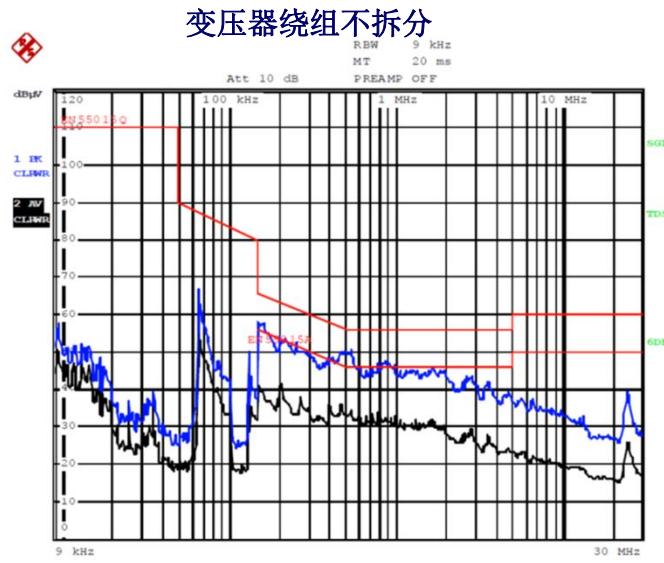
## 传导 (Conducted EMI)

- ❖ 减小传导电磁干扰途径 – 改变变压器结构



# 传导 (Conducted EMI)

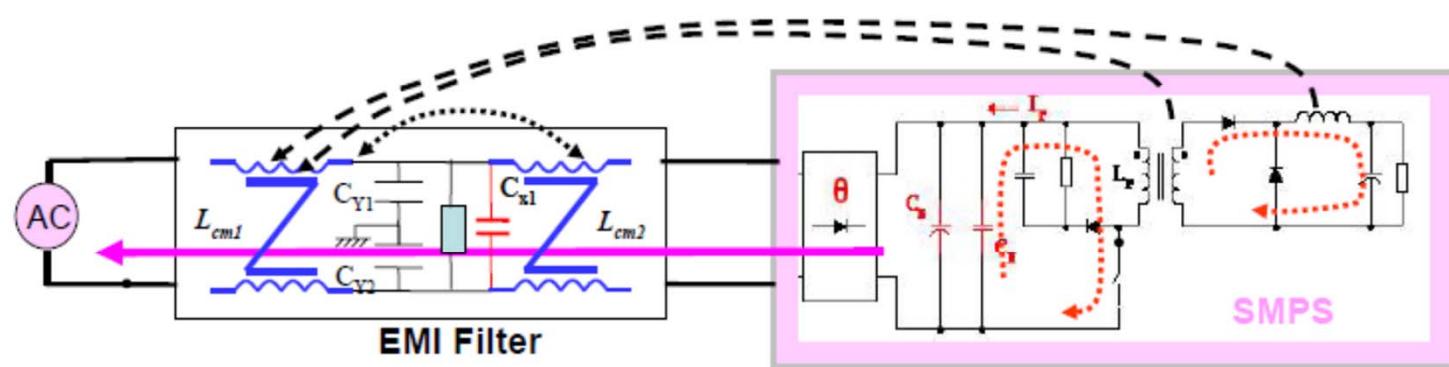
- ❖ 减小传导电磁干扰途径四 – 改变变压器结构



在通过将变压器的一个绕组拆分为两部分，200kHz 至 5MHz 有大约 6dB 的改善.

## 传导 (Conducted EMI)

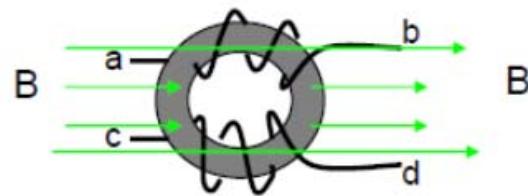
- ❖ 近场耦合效应



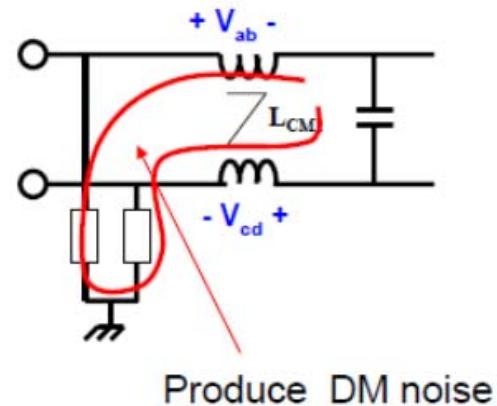
- Coupling inside EMI filter: CMC to CMC, CMC to Cap, Cap to Cap.
- Coupling between EMI filter and transformer/inductor.

# 传导 (Conducted EMI)

- ❖ 近场耦合效应



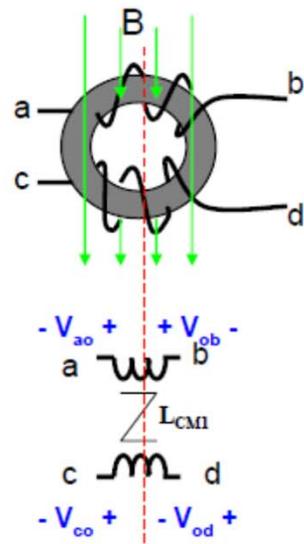
$$\begin{matrix} + V_{ab} & - \\ a & \text{---} \\ & \diagup \\ & L_{CM} \\ & \diagdown \\ c & \text{---} \\ - V_{cd} & + \end{matrix}$$



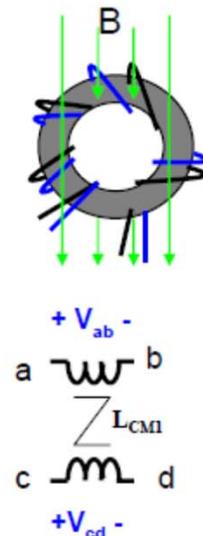
# 传导 (Conducted EMI)

- ❖ 近场耦合效应

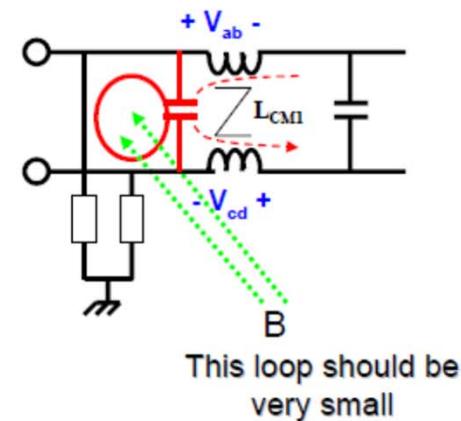
方案1  
改变共模电感方向



方案2  
共模电感双线并绕



方案3  
共模电感前加电容



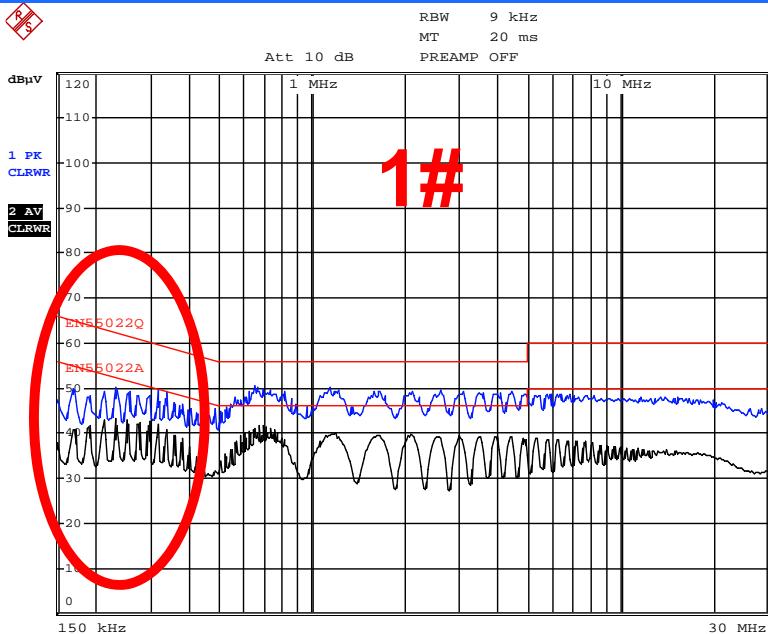
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- ❖ 近场耦合效应

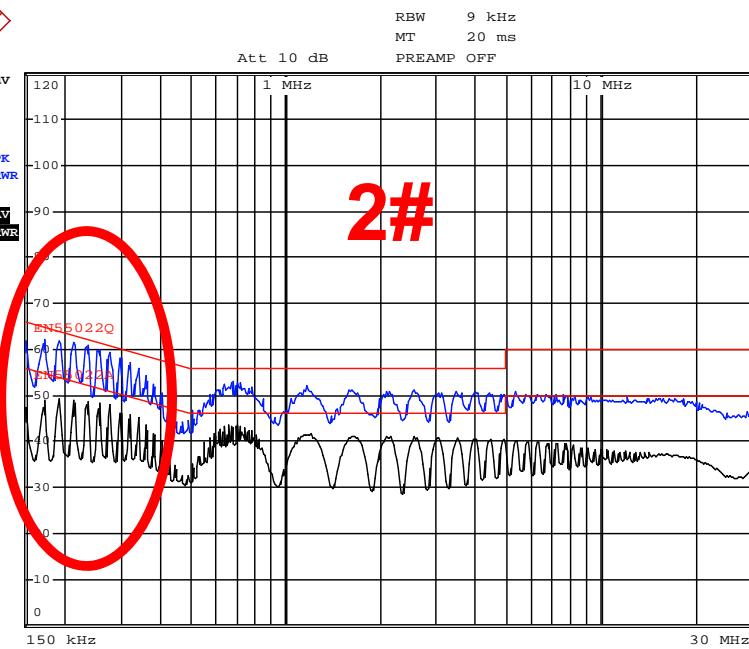


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# 传导 (Conducted EMI)

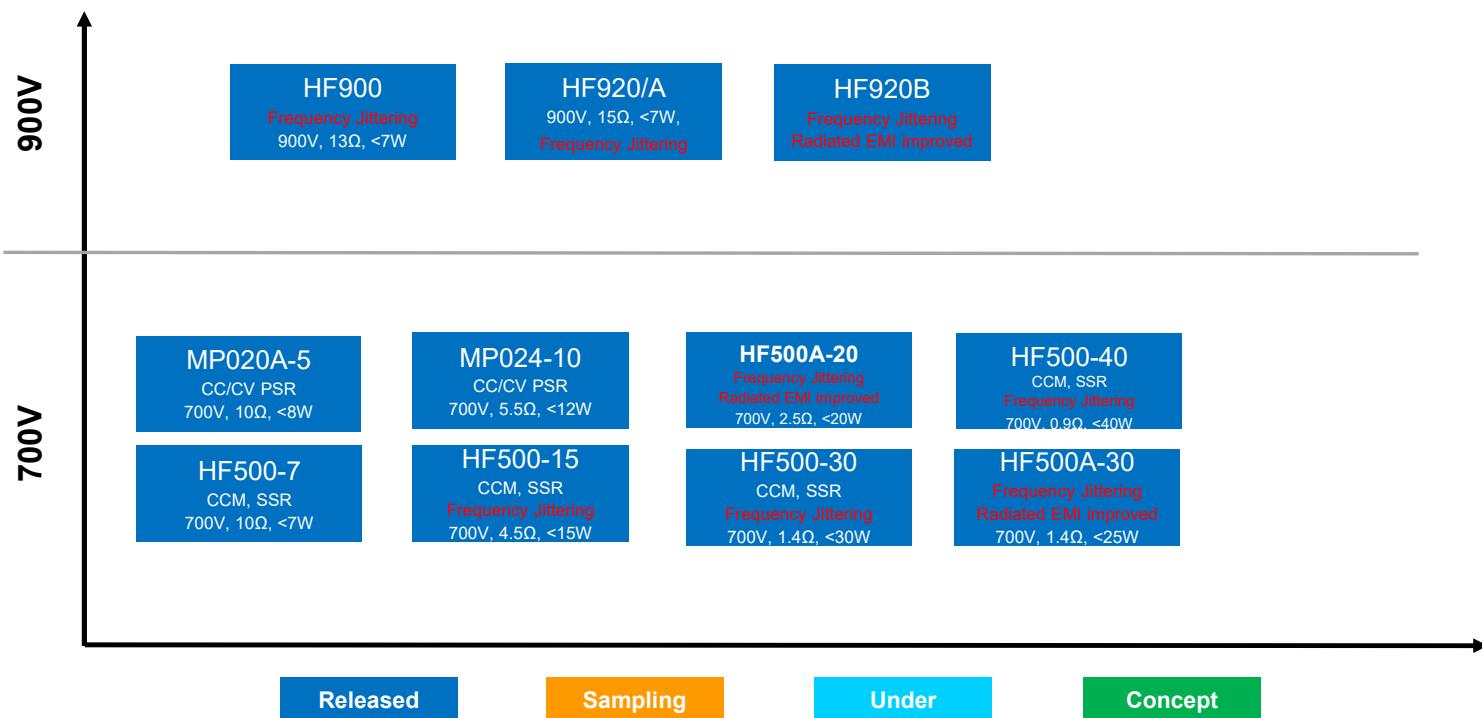


+10dB improvement



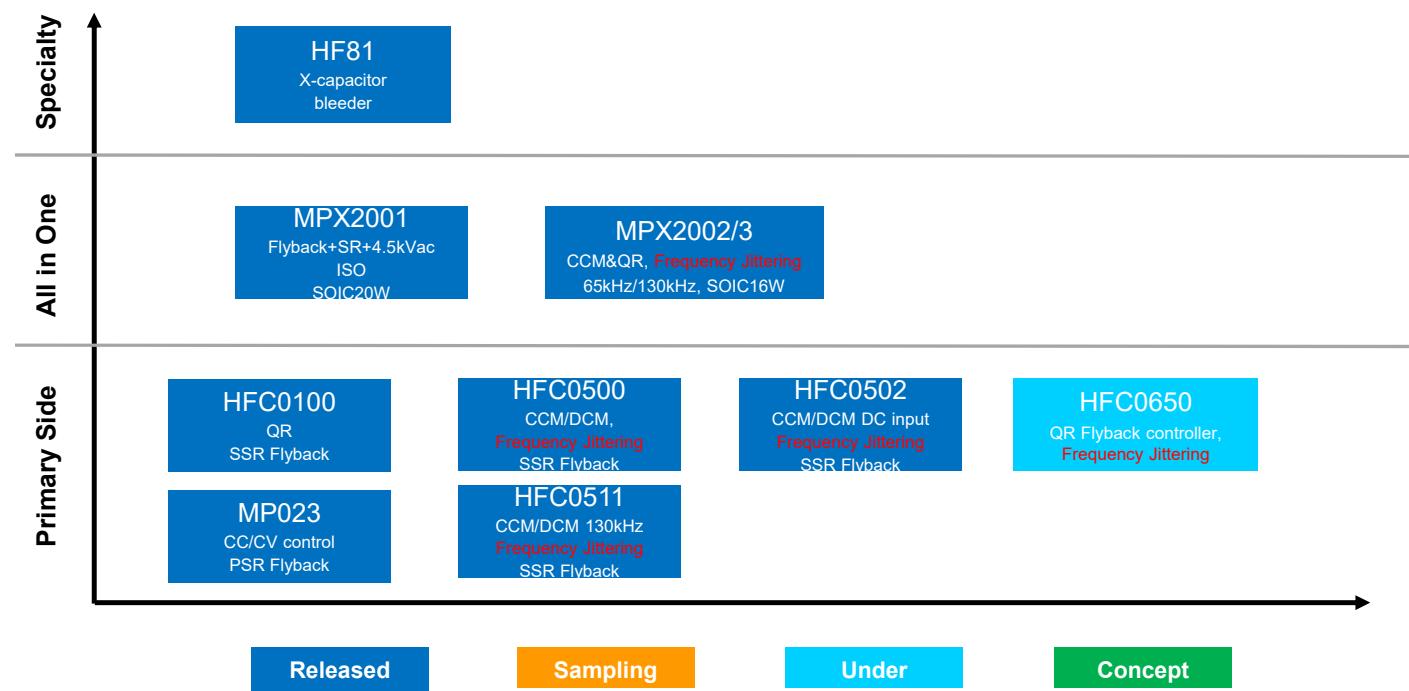
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# AC/DC Flyback regulator with integrated MOSFET, up to 40W



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# AC/DC Flyback Controller, up to 140W



**mPS**

# Q&A

**mPS**